

Improvement of Coherent Scattering Microscopy by applying Ptychographical Iterative Engine

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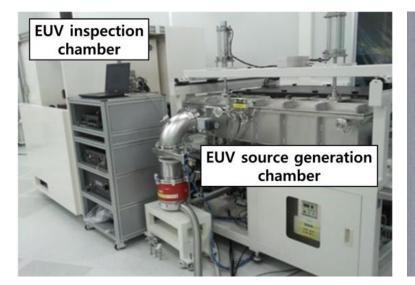
- **1. Introduction**
- 2. Ptychographical iterative engine (PIE)
- **3. Modified PIE**
- 4. Hardware improvement
- 5. Summary



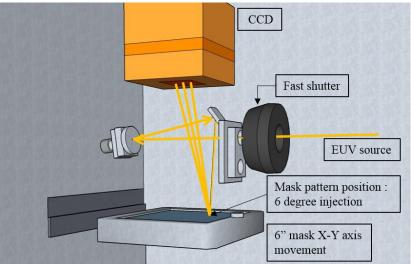
Introduction



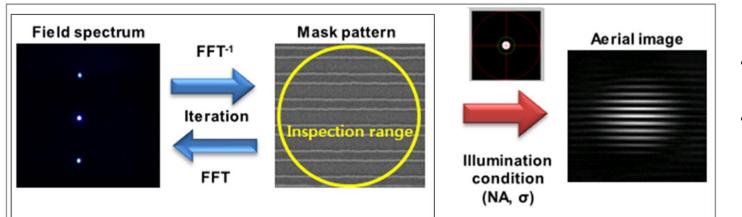
Coherent Scattering Microscopy (CSM)



< Coherent scattering microscopy >



< Optic chamber of CSM >



EUV scannerCSMWavelengths (nm)13.513.5Incidence angle (°)66Numerical aperture0.33 (NXE:3300)0.59 (max)IlluminationVariousVarious

< Comparison between EUV scanner and CSM >

- Evaluation mask imaging performance by actinic inspection
- Lensless imaging free from the errors that occur from lens imperfections

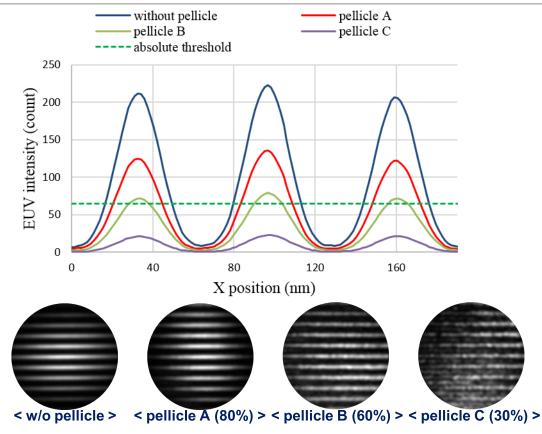


< Image reconstruction method >

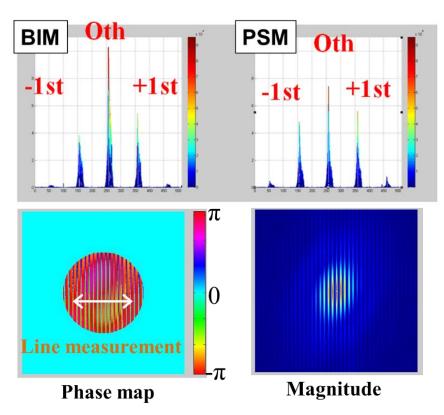


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Capability of CSM



< Evaluation of imaging performance of EUV mask with pellicle >



< Extracting phase map of EUV mask >

- Inspection tool for analyzing the phase shift effect of PSM is insufficient
- Field of view is limited as inspection beam size
 - Achieving the large FOV by applying the ptychography to CSM

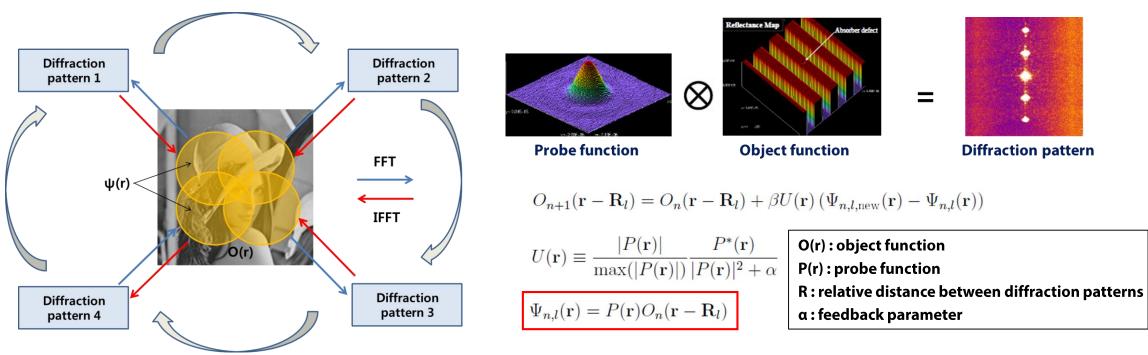




Ptychographic Iterative Engine (PIE)



Principle of Ptychography



< Schematic view of ptychographic iterative engine (PIE) >

< Mathematics in PIE >

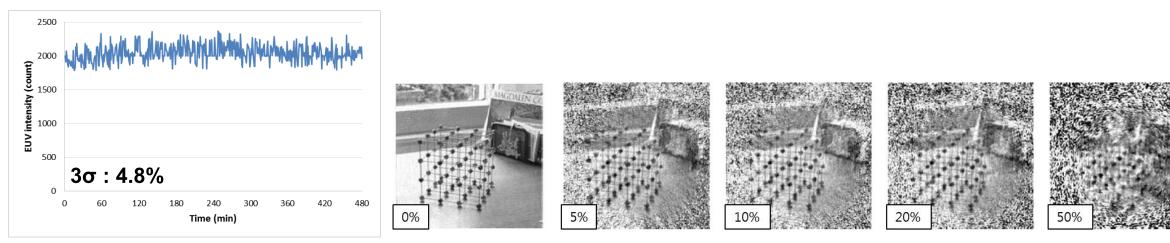
- Separating the probe and object function from diffraction pattern
- Enlargement of FOV by image stitching
- Finite probe & constraint determines resolution of reconstructed image



resolution of reconstructed image

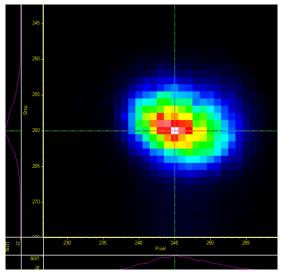


Influence of probe function stability on reconstructed image



< Power stability of inspection source >

< Reconstructed images with random noise in probe function >



< Shape of inspection source >

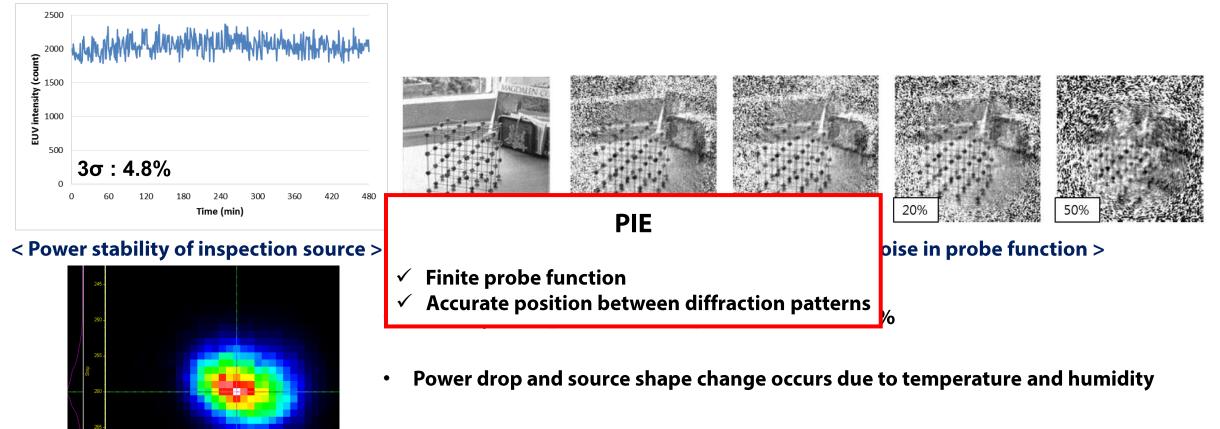
- Stability of inspection source power (8hr) : 3σ 4.8%
- Power drop and source shape change occurs due to temperature and humidity
- Random noise introduced probe function will degrade the resolution of reconstructed image



<Ref. H. M. L. Faulkner, J. M. Rodenburg, Ultramicroscopy 103 (2005)>



Influence of probe function stability on reconstructed image



 Random noise introduced probe function will degrade the resolution of reconstructed image



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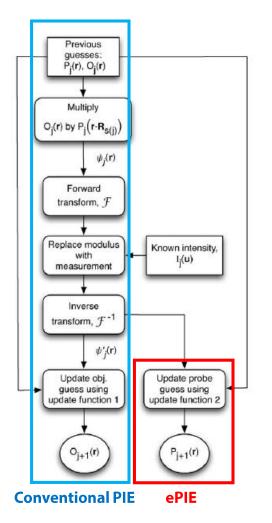
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< Shape of inspection source >

Modified PIE

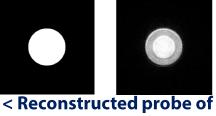


Concept of extended PIE (ePIE)

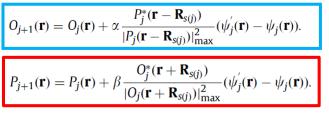




< ground truth & initial guess >



PIE (left) and ePIE (right) >



< Update function of ePIE >



< Reconstructed image of PIE (left) and ePIE (right) >

- Updating probe and object function simultaneously
- Check whether probe function is updated or not
- Resolution of final reconstructed image deteriorates

Insufficient information of redundancy and relative position between diffraction patterns

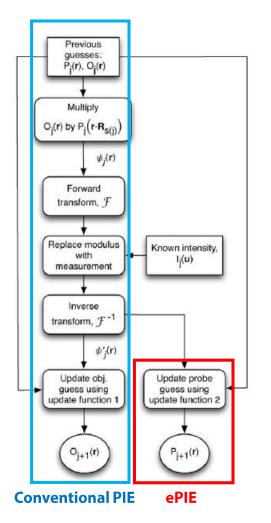
<Ref. F. Hue, J. M. Rodenburg, A. M. Maiden, P. A. Midgley, Ultramicroscopy 111 (2011) >

< Flowchart of ePIE method >



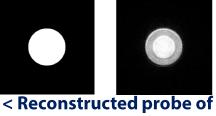
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Concept of extended PIE (ePIE)

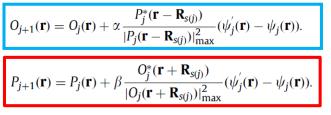




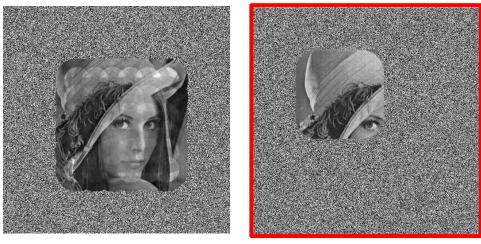
< ground truth & initial guess >



PIE (left) and ePIE (right) >



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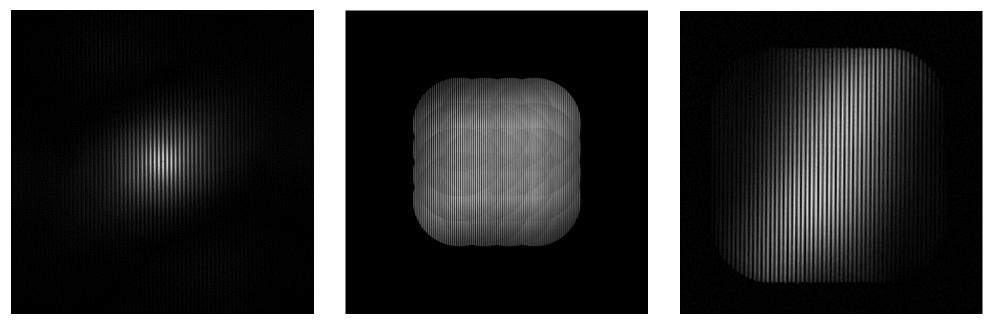
Insufficient information of redundancy and relative position between diffraction patterns

<Ref. F. Hue, J. M. Rodenburg, A. M. Maiden, P. A. Midgley, Ultramicroscopy 111 (2011) >

< Flowchart of ePIE method >



Comparison between PIE and ePIE



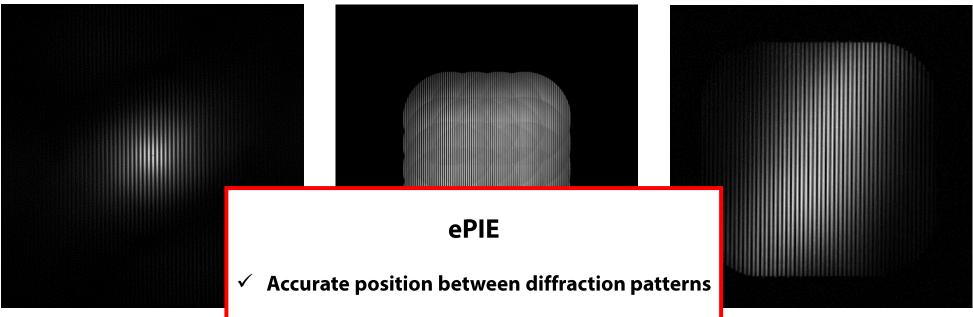
< Reconstructed image of HIO (left), PIE (middle) and ePIE (right) >

- HIO Limited FOV as size of inspection source
- PIE deterioration of reconstructed image resolution and boundary occurrence due to inaccurate probe function
- ePIE Improvement of reconstructed image resolution but, still insufficient

Should achieve the reliance of relative distance between diffraction pattern



Comparison between PIE and ePIE



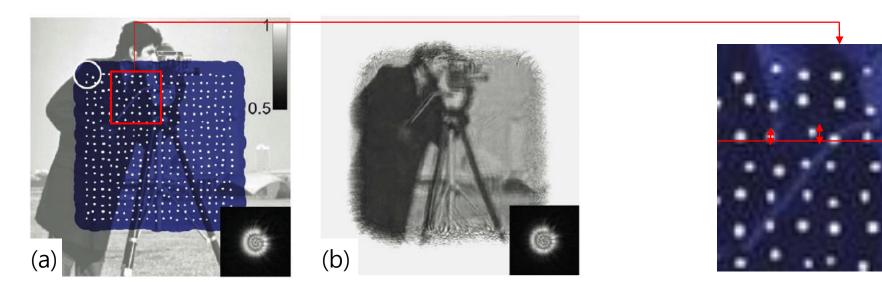
< Reconstructed image of HIO (left), PIE (middle) and ePIE (right) >

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Influence of position accuracy on reconstructed image



Position error due to position accuracy of stage and thermal drift

< Image reconstructed by ePIE with position error induced diffraction pattern >

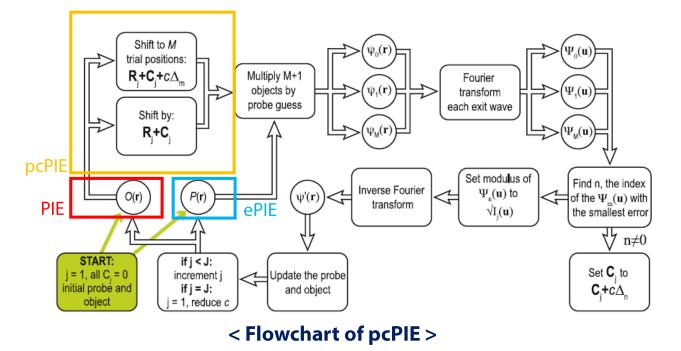
- Tolerance of position error on PIE and ePIE is 1% of step size
- Size of CSM inspection source is 1.5µm, when secure 60% redundancy its step size is 0.6µm and to prevent resolution degradation 6nm position accuracy is required
- Inevitable error which is out of stage position accuracy specification

Compensation method through algorithm improvement should be studied

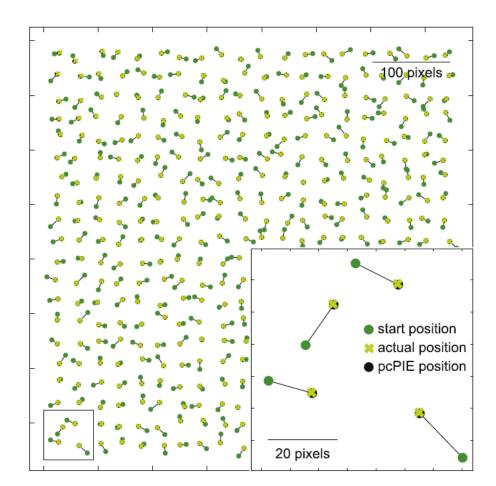
<Ref. A. M. Maiden, M. J. Humphry, M. C. Sarahan, B. Kraus, and J. M. Rodenburg, Ultramicroscopy 120 (2012) >



Concept of position correcting PIE (pcPIE)



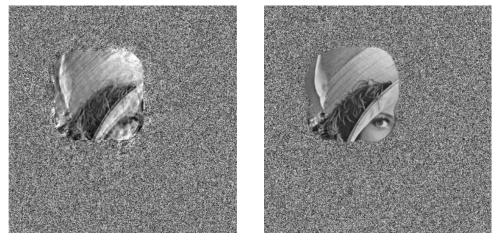
- pcPIE iteratively updates the initial object and probe like ePIE, and additionally updates the position simultaneously
- The resolution and accuracy of ptychographic images are restricted by the precision of the specimen positions



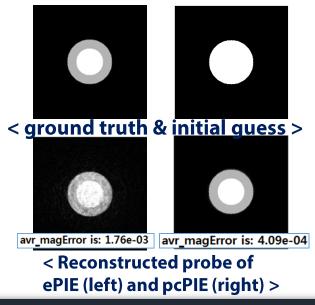
< Position correcting results of pcPIE >

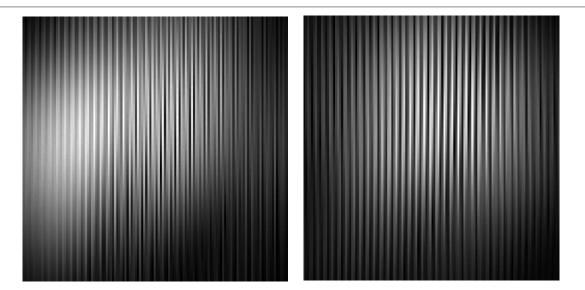
< Ref. A. M. Maiden, M. J. Humphry, M. C. Sarahan, B. Kraus, and J. M. Rodenburg, Ultramicroscopy 120 (2012) >

Reconstructed images using pcPIE



< Image reconstructed by ePIE (left) and pcPIE(right) with position error induced diffraction pattern >





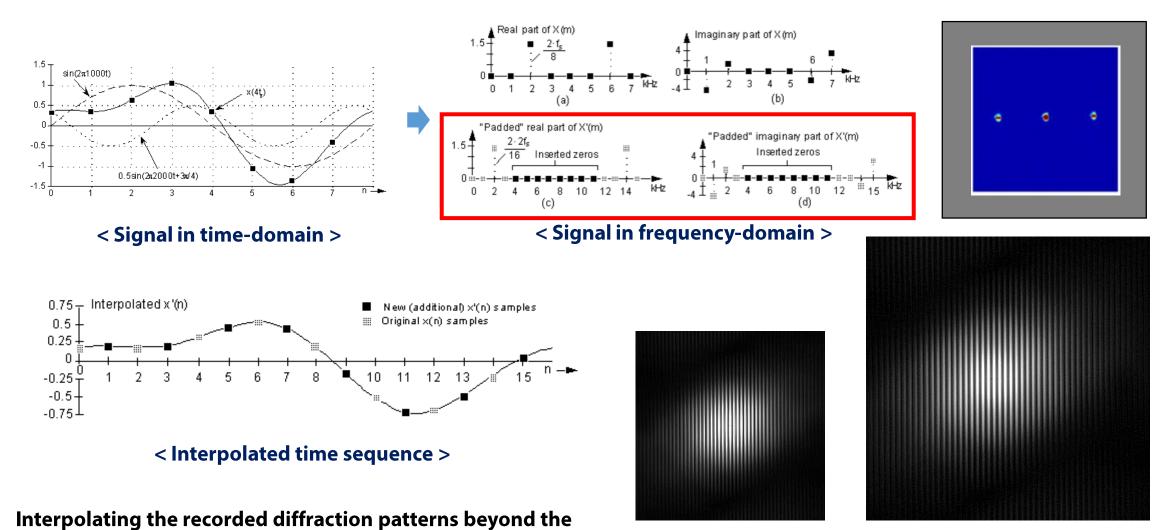
< Image reconstructed by ePIE (left) and pcPIE(right) with diffraction pattern captured by CSM, 128 nm hp L/S EUV mask>

- Improvement of reconstructed image resolution by compensating inaccuracy of translation stage
- Noise of reconstructed probe function is also alleviated
- Tolerance of position accuracy could be relieved from 1% to 15% of step size



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superresolution PIE (SR-PIE)



- < Reconstructed image applying interpolating>
- aperture of the detector is considered to enhance resolution of ptychography

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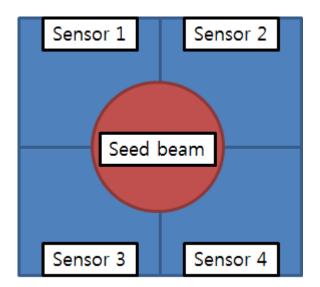
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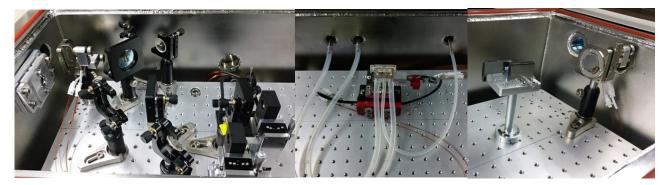
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Hardware improvement



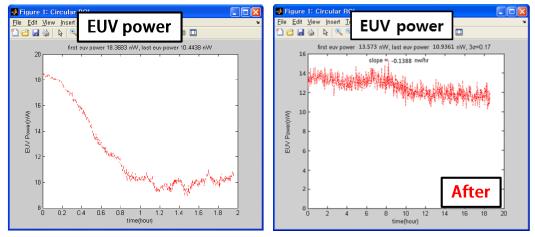
Source stabilizer system



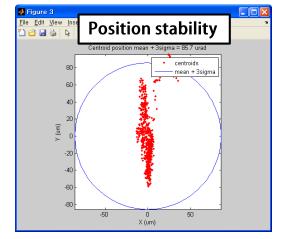


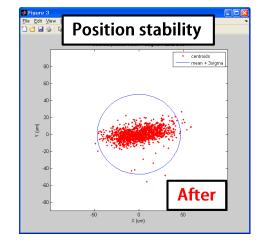
< EUV stabilizer system >

< Concept of EUV stabilizer system >



< Long-term stability after applying EUV stabilizer system >

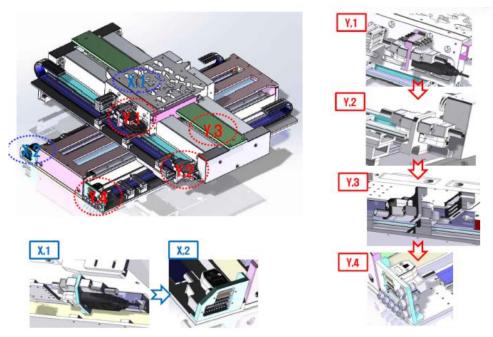




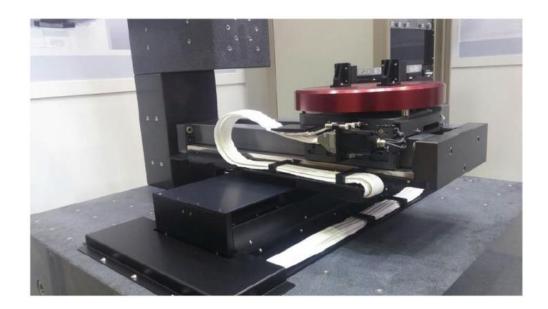
< Long-term position stability after applying EUV stabilizer system >



High precision stage



< Schematic of the designed stage >



< Proto-type of high precision stage >

- Designing precision stage to minimize the physical position error
- Position accuracy within in 100 nm to achieve reliance of relative distance between diffraction pattern
- Sub micron resolution to achieve enough redundancy



- Coherent Scattering Microscopy (CSM) is verified actinic inspection tool for evaluating the imaging performance but, it is limited by its field of view
- Ptychography is applied to CSM to enlarge field of view
- Using ePIE, accuracy of reconstructed probe function is improved.
- Experimental error such as beam instability and position inaccuracy has been compensated by using modified PIE (1% → 15% tolerance of position error)
- High precision hardware have been established to minimize the mechanical error



Thank you for your attention. Question and Answer

